

SMD Schottky Barrier Diode

COMCHIP
SMD Diodes Specialist

CDBU0530 (RoHS Device)

I_o = 500 mA

V_R = 20 Volts



Features

Low forward voltage.

Designed for mounting on small surface.

Extremely thin / leadless package.

Majority carrier conduction.

Mechanical data

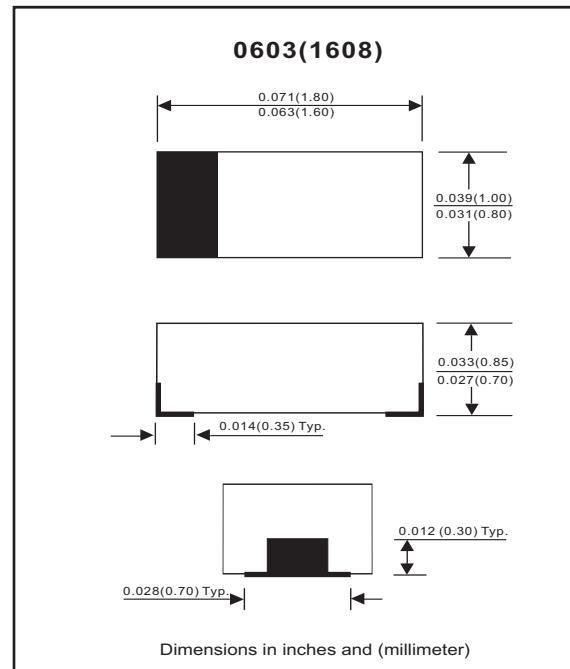
Case: 0603(1608) standard package,
molded plastic.

Terminals: Gold plated, solderable per
MIL-STD-750, method 2026.

Polarity: Indicated by cathode band.

Mounting position: Any

Weight: 0.003 gram(approx.).



Maximum Rating (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Peak reverse voltage		V _{RM}			30	V
Reverse voltage		V _R			20	V
Average forward rectified current		I _o			0.5	A
Forward current,surge peak	8.3 ms single half sine-wave superimposed on rate load (JEDEC method)	I _{FSM}			2	A
Storage temperature		T _{STG}	-40		+125	°C
Junction temperature		T _j			+125	°C

Electrical Characteristics (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F = 100mA I _F = 500mA	V _F			0.36 0.47	V
Reverse current	V _R = 20V	I _R			100	uA
Capacitance between terminals	f = 1 MHz, and 0 VDC reverse voltage	C _T		100		pF

RATING AND CHARACTERISTIC CURVES (CDBU0530)

Fig. 1 - Forward characteristics

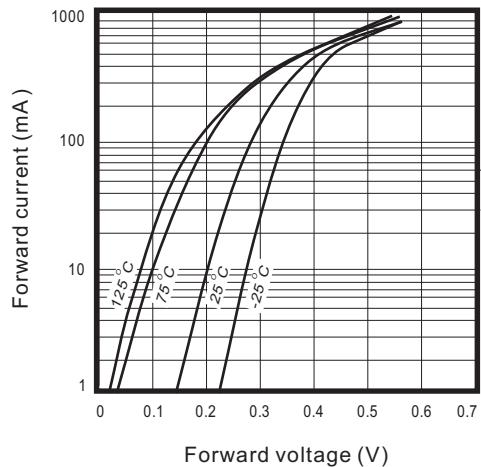


Fig. 2 - Reverse characteristics

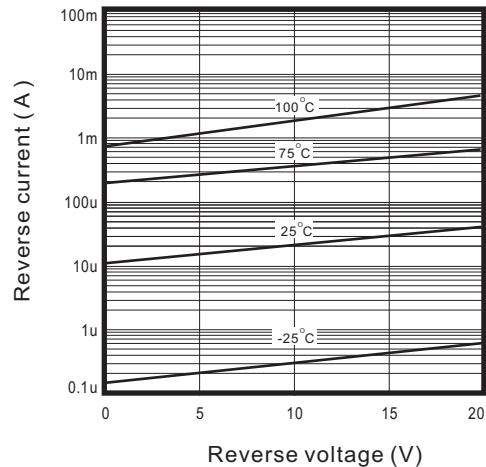


Fig. 3 - Capacitance between terminals characteristics

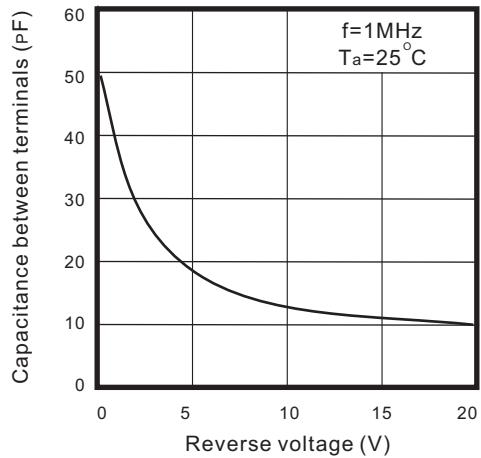


Fig.4 - Current derating curve

